

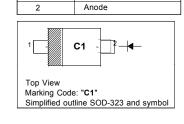
DESCRIPTION Cathode

1SS352 Silicon Epitaxial Planar Switching Diode

Features

- · Low forward voltage
- Fast Reverse Recovery Time
- Small TotalCapacitance

Application



PINNING

PIN

1

• Ultra high speed switching

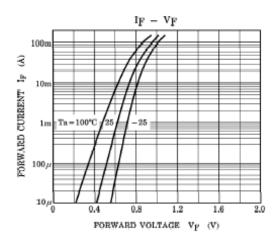
Absolute Maximum Ratings (T_a = 25 °C)

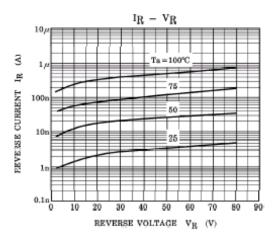
Parameter	Symbol	Value	Unit
Maximum (Peak) Reverse Voltage	V _{RM}	85	V
Reverse Voltage	V _R	80	V
Average Rectified Forward Current	I _{F(AV)}	100	mA
Maximum (Peak) Forward Current	I _{FM}	200	mA
Surge Forward Current (10 ms)	I _{FSM}	1	А
Power Dissipation	P _{tot}	200	mW
Junction Temperature	Tj	150	°C
Storage Temperature Range	T _{stg}	- 55 to + 150	°C

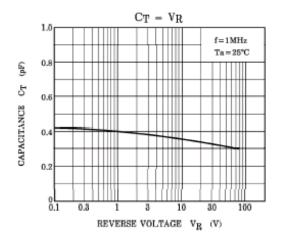
Characteristics at $T_a = 25 \circ C$

Parameter	Symbol	Max.	Unit
Forward Voltage at I _F = 100 mA	V _F	1.2	V
Reverse Current at $V_R = 30 V$ at $V_R = 80 V$	۱ _R	0.1 0.5	μA
Total Capacitance at V _R = 0 V, f = 1 MHz	CT	3	pF
Reverse Recovery Time at I _F = 10 mA to I _R = 1 mA, V _R = 6 V, R _L = 100 Ω	t _{rr}	4	ns







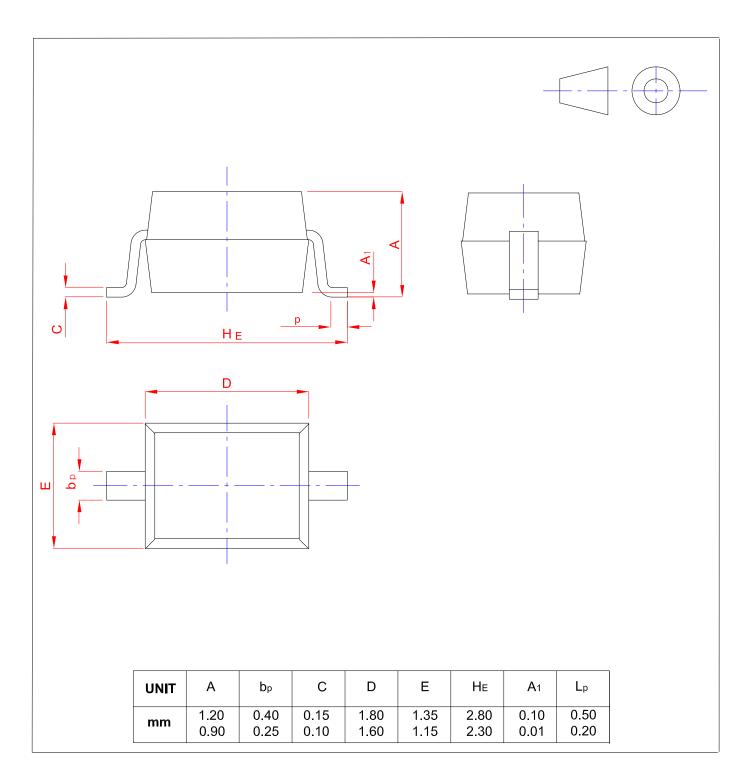




SOD-323

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads



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